

Micron		Digi+Reel		FLASH (suite) Conforme à RoHS			
N° de référence Micron Technology	N° de référence Digi-Key	Description		Boîtier	Prix unitaire★		
					1	25	100
MT29F4G08ABCWC-ET-C TR	557-1366-2-ND	4 Gb, 1.8 V	4Gb, 1.8V	48-TSOP		6969.96/1,000	
MT29F4G16AACWC.C TR	557-1367-1-ND	4 Gb, 3.3 V	4Gb, 3.3V	48-TSOP	10.13	7.61	6.99
MT29F4G16AACWC.C TR	557-1367-2-ND	4 Gb, 3.3 V	4Gb, 3.3V	48-TSOP		6388.92/1,000	
MT29F4G16AACWC-ET-C TR	557-1368-1-ND	4 Gb, 3.3 V	4Gb, 3.3V	48-TSOP	11.05	8.30	7.62
MT29F4G16AACWC-ET-C TR	557-1368-2-ND	4 Gb, 3.3 V	4Gb, 3.3V	48-TSOP		6969.96/1,000	
MT29F4G16ABCHC.C TR	557-1369-1-ND	4 Gb, 1.8 V	4Gb, 1.8V	63-VFBGA	11.05	8.30	7.62
MT29F4G16ABCHC.C TR	557-1369-2-ND	4 Gb, 1.8 V	4Gb, 1.8V	63-VFBGA		6969.96/1,000	
MT29F4G16ABCHC-ET-C TR	557-1370-1-ND	4 Gb, 1.8 V	4Gb, 1.8V	63-VFBGA	11.05	8.30	7.62
MT29F4G16ABCHC-ET-C TR	557-1370-2-ND	4 Gb, 1.8 V	4Gb, 1.8V	63-VFBGA		6969.96/1,000	
MT29F8G08AAAWP-A TR	557-1371-1-ND	8 Gb, 3.3 V	8Gb, 3.3V	48-TSOP	14.59	10.96	10.06
MT29F8G08AAAWP-A TR	557-1371-2-ND	8 Gb, 3.3 V	8Gb, 3.3V	48-TSOP		9200.96/1,000	
MT29F8G08AAAWP-ET-A TR	557-1372-1-ND	8 Gb, 3.3 V	8Gb, 3.3V	48-TSOP	16.13	12.11	11.12
MT29F8G08AAAWP-ET-A TR	557-1372-2-ND	8 Gb, 3.3 V	8Gb, 3.3V	48-TSOP		10169.08/1,000	
MT29F8G08MAAWC-ET-B TR	557-1373-1-ND	8 Gb, 3.3 V	8Gb, 3.3V	48-TSOP	8.90	6.69	6.14
MT29F8G08MAAWC-ET-B TR	557-1373-2-ND	8 Gb, 3.3 V	8Gb, 3.3V	48-TSOP		5614.76/1,000	
MT29F8G08MADWC-D TR	557-1414-1-ND	8 Gb, 3.3 V	8Gb, 3.3V	48-TSOP	8.52	5.77	5.48
MT29F8G08MADWC-D TR	557-1414-2-ND	8 Gb, 3.3 V	8Gb, 3.3V	48-TSOP		4960.88/1,000	
MT29F16G08DAAWP-ET-A TR	557-1413-1-ND	16 Gb, 3.3 V	16Gb, 3.3V	48-TSOP	33.91	28.05	26.30
MT29F16G08DAAWP-ET-A TR	557-1413-2-ND	16 Gb, 3.3 V	16Gb, 3.3V	48-TSOP		24313.14/1,000	
MT29F16G08MAAWP-A TR	557-1374-1-ND	16 Gb, 3.3 V	16Gb, 3.3V	48-TSOP	13.06	9.80	9.00
MT29F16G08MAAWP-A TR	557-1374-2-ND	16 Gb, 3.3 V	16Gb, 3.3V	48-TSOP		8232.84/1,000	
MT29F32G08AAAWP-A TR	557-1375-1-ND	32 Gb, 3.3 V	32Gb, 3.3V	48-TSOP	23.89	18.61	17.47
MT29F32G08AAAWP-A TR	557-1375-2-ND	32 Gb, 3.3 V	32Gb, 3.3V	48-TSOP		16072.67/1,000	

Micron		Digi+Reel		PSRAM Conforme à RoHS			
N° de référence Micron Technology	N° de référence Digi-Key	Description		Boîtier	Prix unitaire★		
					1	25	100
MT45V256KW16PEGA-55 WT TR	557-1415-1-ND	PSRAM à mode page/asynchrone, noyau 3 V, 4 Mb	3.0V Core Async./Page PSRAM 4Mb	48-VFBGA	3.03	1.93	1.74
MT45V256KW16PEGA-55 WT TR	557-1415-2-ND	PSRAM à mode page/asynchrone, noyau 3 V, 4 Mb	3.0V Core Async./Page PSRAM 4Mb	48-VFBGA		1546.62/1,000	
MT45V256KW16PEGA-70 WT TR	557-1416-1-ND	PSRAM à mode page/asynchrone, noyau 3 V, 4 Mb	3.0V Core Async./Page PSRAM 4Mb	48-VFBGA	2.82	1.80	1.62
MT45V256KW16PEGA-70 WT TR	557-1416-2-ND	PSRAM à mode page/asynchrone, noyau 3 V, 4 Mb	3.0V Core Async./Page PSRAM 4Mb	48-VFBGA		1438.21/1,000	
MT45V512KW16PEGA-55 WT TR	557-1417-1-ND	PSRAM à mode page/asynchrone, noyau 3 V, 8 Mb	3.0V Core Async./Page PSRAM 8Mb	48-VFBGA	3.03	1.93	1.74
MT45V512KW16PEGA-55 WT TR	557-1417-2-ND	PSRAM à mode page/asynchrone, noyau 3 V, 8 Mb	3.0V Core Async./Page PSRAM 8Mb	48-VFBGA		1546.62/1,000	
MT45V512KW16PEGA-70 WT TR	557-1418-1-ND	PSRAM à mode page/asynchrone, noyau 3 V, 8 Mb	3.0V Core Async./Page PSRAM 8Mb	48-VFBGA	2.82	1.80	1.62
MT45V512KW16PEGA-70 WT TR	557-1418-2-ND	PSRAM à mode page/asynchrone, noyau 3 V, 8 Mb	3.0V Core Async./Page PSRAM 8Mb	48-VFBGA		1438.21/1,000	
MT45W1MW16B8B-706 WT TR	557-1006-1-ND	Mémoire à mode d'accès async/page/en rafale CellularRAM™, 16 Mb	Async./Page/Burst CellularRAM™, 16Mb	54-VFBGA	4.27	2.95	2.71
MT45W1MW16B8B-706 WT TR	557-1006-2-ND	Mémoire à mode d'accès async/page/en rafale CellularRAM™, 16 Mb	Async./Page/Burst CellularRAM™, 16Mb	54-VFBGA		2490.18/1,000	
MT45W1MW16B8B-701 WT TR	557-1209-1-ND	Mémoire à mode d'accès async/page/en rafale CellularRAM™, 16 Mb	Async./Page/Burst CellularRAM™, 16Mb	54-VFBGA	3.84	2.44	2.20
MT45W1MW16B8B-701 WT TR	557-1209-2-ND	Mémoire à mode d'accès async/page/en rafale CellularRAM™, 16 Mb	Async./Page/Burst CellularRAM™, 16Mb	54-VFBGA		1957.44/1,000	
MT45W1MW16B8B-708 AT TR	557-1419-1-ND	Mémoire à mode d'accès async/page/en rafale CellularRAM™, 16 Mb	Async./Page/Burst CellularRAM™, 16Mb	54-VFBGA	4.02	2.56	2.31
MT45W1MW16B8B-708 AT TR	557-1419-2-ND	Mémoire à mode d'accès async/page/en rafale CellularRAM™, 16 Mb	Async./Page/Burst CellularRAM™, 16Mb	54-VFBGA		2054.82/1,000	
MT45W1MW16B8B-708 WT TR	557-1274-1-ND	Mémoire à mode d'accès async/page/en rafale CellularRAM™, 16 Mb	Async./Page/Burst CellularRAM™, 16Mb	54-VFBGA	2.82	1.80	1.62
MT45W1MW16B8B-708 WT TR	557-1274-2-ND	Mémoire à mode d'accès async/page/en rafale CellularRAM™, 16 Mb	Async./Page/Burst CellularRAM™, 16Mb	54-VFBGA		1438.21/1,000	
MT45W1MW16P0GA-70 WT TR	557-1275-1-ND	Mémoire à mode d'accès async/page/en rafale CellularRAM™, 16 Mb	Async./Page/Burst CellularRAM™, 16Mb	48-VFBGA	2.82	1.80	1.62
MT45W1MW16P0GA-70 WT TR	557-1275-2-ND	Mémoire à mode d'accès async/page/en rafale CellularRAM™, 16 Mb	Async./Page/Burst CellularRAM™, 16Mb	48-VFBGA		1438.21/1,000	
MT45W2MW16B8B-706 WT TR	557-1007-1-ND	Mémoire à mode d'accès async/page/en rafale CellularRAM™, 32 Mb	Async./Page/Burst CellularRAM™, 32Mb	54-VFBGA	5.07	3.50	3.22
MT45W2MW16B8B-706 WT TR	557-1318-1-ND	Mémoire à mode d'accès async/page/en rafale CellularRAM™, 32 Mb	Async./Page/Burst CellularRAM™, 32Mb	54-VFBGA	4.83	2.91	2.77
MT45W2MW16B8B-708 WT TR	557-1318-2-ND	Mémoire à mode d'accès async/page/en rafale CellularRAM™, 32 Mb	Async./Page/Burst CellularRAM™, 32Mb	54-VFBGA		2466.46/1,000	
MT45W2MW16P6GA-70 IT TR	557-1317-1-ND	Mémoire à mode d'accès async/page/en rafale CellularRAM™, 32 Mb	Async./Page/Burst CellularRAM™, 32Mb	48-VFBGA	5.23	3.15	3.00
MT45W2MW16P6GA-70 IT TR	557-1317-2-ND	Mémoire à mode d'accès async/page/en rafale CellularRAM™, 32 Mb	Async./Page/Burst CellularRAM™, 32Mb	48-VFBGA		2671.44/1,000	
MT45W2MW16P6GA-70 WT TR	557-1316-1-ND	Mémoire à mode d'accès async/page/en rafale CellularRAM™, 32 Mb	Async./Page/Burst CellularRAM™, 32Mb	48-VFBGA	4.83	2.91	2.77
MT45W2MW16P6GA-70 WT TR	557-1316-2-ND	Mémoire à mode d'accès async/page/en rafale CellularRAM™, 32 Mb	Async./Page/Burst CellularRAM™, 32Mb	48-VFBGA		2466.46/1,000	
MT45W4MW16B8B-708 WT TR	557-1172-1-ND	Mémoire à mode d'accès async/page/en rafale CellularRAM™ 1.0	Async./Page/Burst CellularRAM™, 1.0 Memory	54-VFBGA	5.79	4.11	3.73
MT45W4MW16B8B-708 WT TR	557-1172-2-ND	Mémoire à mode d'accès async/page/en rafale CellularRAM™ 1.0	Async./Page/Burst CellularRAM™, 1.0 Memory	54-VFBGA		3373.60/1,000	
MT45W4MW16P0GA-70 WT TR	557-1210-1-ND	Mémoire à mode d'accès async/page/en rafale CellularRAM™, 64 Mb	Async./Page/Burst CellularRAM™, 64Mb	48-VFBGA	5.79	4.11	3.73
MT45W4MW16P0GA-70 WT TR	557-1210-2-ND	Mémoire à mode d'accès async/page/en rafale CellularRAM™, 64 Mb	Async./Page/Burst CellularRAM™, 64Mb	48-VFBGA		3373.60/1,000	
MT45W8MW16B8B-708 WT TR	557-1010-1-ND	Mémoire à mode d'accès async/page/en rafale CellularRAM™, 128 Mb	Async./Page/Burst CellularRAM™, 128Mb	54-VFBGA	7.93	5.37	5.10
MT45W8MW16B8B-708 WT TR	557-1010-2-ND	Mémoire à mode d'accès async/page/en rafale CellularRAM™, 128 Mb	Async./Page/Burst CellularRAM™, 128Mb	54-VFBGA		4616.15/1,000	
MT45W256KW16B8B-708 WT TR	557-1420-1-ND	Mémoire 1.0 à mode d'accès async/page/en rafale CellularRAM™, 4 Mb	Async./Page/Burst CellularRAM™, 1.0 Memory, 4Mb	54-VFBGA	2.82	1.80	1.62
MT45W256KW16B8B-708 WT TR	557-1420-2-ND	Mémoire 1.0 à mode d'accès async/page/en rafale CellularRAM™, 4 Mb	Async./Page/Burst CellularRAM™, 1.0 Memory, 4Mb	54-VFBGA		1438.21/1,000	
MT45W256KW16PEGA-70 WT TR	557-1421-1-ND	Mémoire 1.0 à mode d'accès async/page/en rafale CellularRAM™, 4 Mb	Async./Page/Burst CellularRAM™, 1.0 Memory, 4Mb	48-VFBGA	2.82	1.80	1.62
MT45W256KW16PEGA-70 WT TR	557-1421-2-ND	Mémoire 1.0 à mode d'accès async/page/en rafale CellularRAM™, 4 Mb	Async./Page/Burst CellularRAM™, 1.0 Memory, 4Mb	48-VFBGA		1438.21/1,000	
MT45W512KW16B8B-708 WT TR	557-1422-1-ND	Mémoire 1.0 à mode d'accès async/page/en rafale CellularRAM™, 8 Mb	Async./Page/Burst CellularRAM™, 1.0 Memory, 8Mb	54-VFBGA	2.82	1.80	1.62
MT45W512KW16B8B-708 WT TR	557-1422-2-ND	Mémoire 1.0 à mode d'accès async/page/en rafale CellularRAM™, 8 Mb	Async./Page/Burst CellularRAM™, 1.0 Memory, 8Mb	54-VFBGA		1438.21/1,000	
MT45W512KW16PEGA-70 IT TR	557-1423-1-ND	Mémoire 1.0 à mode d'accès async/page/en rafale CellularRAM™, 8 Mb	Async./Page/Burst CellularRAM™, 1.0 Memory, 8Mb	48-VFBGA	2.92	1.86	1.68
MT45W512KW16PEGA-70 IT TR	557-1423-2-ND	Mémoire 1.0 à mode d'accès async/page/en rafale CellularRAM™, 8 Mb	Async./Page/Burst CellularRAM™, 1.0 Memory, 8Mb	48-VFBGA		1492.41/1,000	
MT45W512KW16PEGA-70 WT TR	557-1424-1-ND	Mémoire 1.0 à mode d'accès async/page/en rafale CellularRAM™, 8 Mb	Async./Page/Burst CellularRAM™, 1.0 Memory, 8Mb	48-VFBGA	2.82	1.80	1.62
MT45W512KW16PEGA-70 WT TR	557-1424-2-ND	Mémoire 1.0 à mode d'accès async/page/en rafale CellularRAM™, 8 Mb	Async./Page/Burst CellularRAM™, 1.0 Memory, 8Mb	48-VFBGA		1438.21/1,000	

Qimonda		SDRAM — Conforme à RoHS — En raison des fluctuations du marché, veuillez vous reporter au site Web Digi-Key pour connaître le tarif le plus récent.					
N° de référence Qimonda	N° de référence Digi-Key	Description		Boîtier	Prix unitaire★		
					1	25	100
HYB39S128160FE-7	675-1002-1-ND	SDRAM, 128 Mb	128Mb SDRAM	54-TSOP	4.49	3.19	2.88
HYB39S128160FE-7	675-1002-2-ND	SDRAM, 128 Mb	128Mb SDRAM	54-TSOP		3916.95/1,500	
HYB39S128800FE-7	675-1001-1-ND	SDRAM, 128 Mb	128Mb SDRAM	54-TSOP	4.49	3.19	2.88
HYB39S128800FE-7	675-1001-2-ND	SDRAM, 128 Mb	128Mb SDRAM	54-TSOP		3916.95/1,500	
HYB39S256160FE-7	675-1004-1-ND	SDRAM, 256 Mb	256Mb SDRAM	54-TSOP	5.74	4.08	3.69
HYB39S256160FE-7	675-1004-2-ND	SDRAM, 256 Mb	256Mb SDRAM	54-TSOP		5013.39/1,500	
HYB39S256800FE-7	675-1003-1-ND	SDRAM, 256 Mb	256Mb SDRAM	54-TSOP	5.74	4.08	3.69
HYB39S256800FE-7	675-1003-2-ND	SDRAM, 256 Mb	256Mb SDRAM	54-TSOP		5013.39/1,500	
HY139S128160FE-7	675-1019-1-ND	SDRAM, 128 Mb	128Mb SDRAM	54-TSOP	5.38	3.82	3.46
HY139S128800FE-7	675-1020-1-ND	SDRAM, 128 Mb	128Mb SDRAM	54-TSOP	5.38	3.82	3.46
HY139S128800FE-7	675-1020-2-ND	SDRAM, 128 Mb	128Mb SDRAM	54-TSOP		4699.58/1,500	
<b>DDR</b>							
HYB25D128800CE-6	675-1005-1-ND	SDRAM DDR, 128 Mb	128Mb DDR SDRAM	66-TSOP	4.98	2.99	2.86
HYB25D128800CE-6	675-1005-2-ND	SDRAM DDR, 128 Mb	128Mb DDR SDRAM	66-TSOP		3681.91/1,500	
HYB25D256160CE-5	675-1006-1-ND	SDRAM DDR, 256 Mb	256Mb DDR SDRAM	66-TFBGA	5.38	3.82	3.46
HYB25D256160CE-5	675-1006-2-ND	SDRAM DDR, 256 Mb	256Mb DDR SDRAM	66-TFBGA		4699.58/1,500	
HYB25D512160CE-5	675-1010-1-ND	SDRAM DDR, 512 Mb	512Mb DDR SDRAM	66-TSOP	9.86	7.40	6.80
HYB25D512160CE-5	675-1010-2-ND	SDRAM DDR, 512 Mb	512Mb DDR SDRAM	66-TSOP		9300.06/1,500	
HYB25D512800CE-5	675-1009-1-ND	SDRAM DDR, 512 Mb	512Mb DDR SDRAM	66-TSOP	9.86	7.40	6.80
HYB25D512800CE-5	675-1009-2-ND	SDRAM DDR, 512 Mb	512Mb DDR SDRAM	66-TSOP		9300.06/1,500	
HYB25D512800CE-6	675-1008-1-ND	SDRAM DDR, 512 Mb	512Mb DDR SDRAM	66-TSOP	9.86	7.40	6.80
HYB25D512800CE-6	675-1008-2-ND	SDRAM DDR, 512 Mb	512Mb DDR SDRAM	66-TSOP		9300.06/1,500	
HY125D256160CE-5	675-1021-1-ND	SDRAM DDR, 256 Mb	256Mb DDR SDRAM	66-TSOP	6.28	4.46	4.04
HY125D256160CE-5	675-1021-2-ND	SDRAM DDR, 256 Mb	256Mb DDR SDRAM	66-TSOP		5336.10/1,500	
HY125D512160CE-5	675-1022-1-ND	SDRAM DDR, 512 Mb	512Mb DDR SDRAM	66-TSOP	11.32	8.50	7.80
HY125D512160CE-5	675-1022-2-ND	SDRAM DDR, 512 Mb	512Mb DDR SDRAM	66-TSOP		10672.20/1,500	
<b>DDR2</b>							
HYB18T1G160BF-5	675-1018-1-ND	SDRAM DDR2, 1 Gb	1Gb DDR2 SDRAM	84-TFBGA	40.40	33.42	31.34
HYB18T1G800BF-3S	675-1017-1-ND	SDRAM DDR2, 1 Gb	1Gb DDR2 SDRAM	68-TFBGA	40.40	33.42	31.34
HYB18T1G800BF-3S	675-1017-2-ND	SDRAM DDR2, 1 Gb	1Gb DDR2 SDRAM	68-TFBGA		60984.00/2,000	
HYB18T512160BF-2.5	675-1016-1-ND	SDRAM DDR2, 512 Mb	512Mb DDR2 SDRAM	84-TFBGA	14.54	10.92	10.03
HYB18T512160BF-3.7	675-1014-1-ND	SDRAM DDR2, 512 Mb	512Mb DDR2 SDRAM	84-TFBGA	10.18	7.65	7.02
HYB18T512160BF-3.7	675-1014-2-ND	SDRAM DDR2					